



256K x 16 Static RAM

Features

- **High speed**
— $t_{AA} = 12 \text{ ns}$
- **Low active power**
— **612 mW (max.)**
- **Low CMOS standby power (Commercial L version)**
— **1.8 mW (max.)**
- **2.0V Data Retention (600 μW at 2.0V retention)**
- **Automatic power-down when deselected**
- **TTL-compatible inputs and outputs**
- **Easy memory expansion with $\overline{\text{CE}}$ and $\overline{\text{OE}}$ features**

Functional Description

The CY7C1041BV33 is a high-performance CMOS Static RAM organized as 262,144 words by 16 bits.

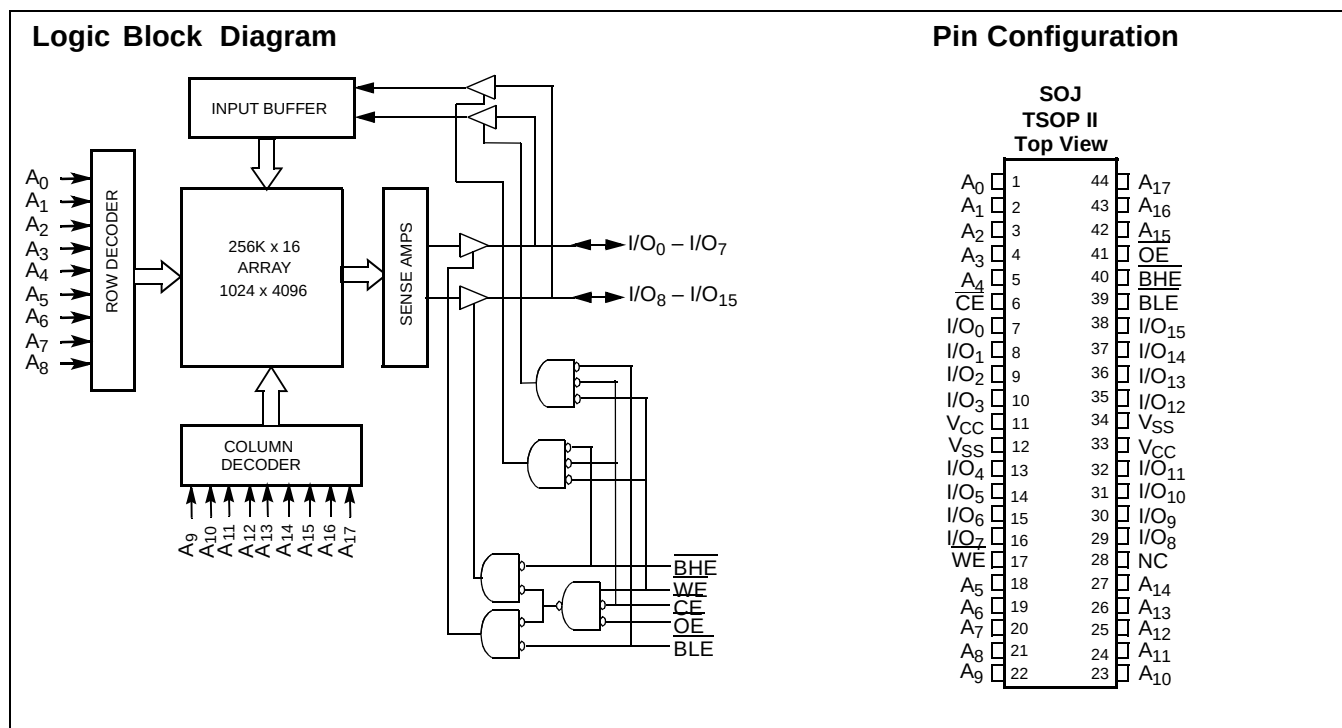
Writing to the device is accomplished by taking Chip Enable ($\overline{\text{CE}}$) and Write Enable ($\overline{\text{WE}}$) inputs LOW. If Byte Low Enable ($\overline{\text{BLE}}$) is LOW, then data from I/O pins (I/O₀ through I/O₇), is

written into the location specified on the address pins (A₀ through A₁₇). If Byte High Enable ($\overline{\text{BHE}}$) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address pins (A₀ through A₁₇).

Reading from the device is accomplished by taking Chip Enable ($\overline{\text{CE}}$) and Output Enable ($\overline{\text{OE}}$) LOW while forcing the Write Enable ($\overline{\text{WE}}$) HIGH. If Byte Low Enable ($\overline{\text{BLE}}$) is LOW, then data from the memory location specified by the address pins will appear on I/O₀ to I/O₇. If Byte High Enable ($\overline{\text{BHE}}$) is LOW, then data from memory will appear on I/O₈ to I/O₁₅. See the truth table at the back of this data sheet for a complete description of read and write modes.

The input/output pins (I/O₀ through I/O₁₅) are placed in a high-impedance state when the device is deselected ($\overline{\text{CE}}$ HIGH), the outputs are disabled ($\overline{\text{OE}}$ HIGH), the $\overline{\text{BHE}}$ and $\overline{\text{BLE}}$ are disabled ($\overline{\text{BHE}}$, $\overline{\text{BLE}}$ HIGH), or during a write operation ($\overline{\text{CE}}$ LOW, and $\overline{\text{WE}}$ LOW).

The CY7C1041BV33 is available in a standard 44-pin 400-mil-wide body width SOJ and 44-pin TSOP II package with center power and ground (revolutionary) pinout.



Selection Guide

		-12	-15	-17	-20	-25
Maximum Access Time (ns)		12	15	17	20	25
Maximum Operating Current (mA)	Comm'l	190	170	160	150	130
	Ind'l	-	190	180	170	150
Maximum CMOS Standby Current (mA)	Com'l/Ind'l	8	8	8	8	8
	Com'l L	0.5	0.5	0.5	0.5	0.5

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with Power Applied..... -55°C to +125°C

Supply Voltage on V_{CC} to Relative GND^[1] -0.5V to +4.6V

DC Voltage Applied to Outputs in High Z State^[1] -0.5V to $V_{CC} + 0.5V$

DC Input Voltage^[1] -0.5V to $V_{CC} + 0.5V$

Current into Outputs (LOW) 20 mA

Operating Range

Range	Ambient Temperature ^[2]	V_{CC}
Commercial	0°C to +70°C	3.3V ± 0.3V
Industrial	-40°C to +85°C	

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	-12		-15		Unit
			Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{Min.}, I_{OH} = -4.0 \text{ mA}$	2.4		2.4		V
V_{OL}	Output LOW Voltage	$V_{CC} = \text{Min.}, I_{OL} = 8.0 \text{ mA}$		0.4		0.4	V
V_{IH}	Input HIGH Voltage		2.2	$V_{CC} + 0.5$	2.2	$V_{CC} + 0.5$	V
V_{IL}	Input LOW Voltage ^[1]		-0.5	0.8	-0.5	0.8	V
I_{IX}	Input Load Current	$GND \leq V_I \leq V_{CC}$	-1	+1	-1	+1	μA
I_{OZ}	Output Leakage Current	$GND \leq V_{OUT} \leq V_{CC}$, Output Disabled	-1	+1	-1	+1	μA
I_{CC}	V_{CC} Operating Supply Current	$V_{CC} = \text{Max.}, f = f_{MAX} = 1/t_{RC}$		190		170	mA
		Comm'l		-		190	
I_{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V_{CC} , $\overline{CE} \geq V_{IH}$ $V_{IN} \geq V_{IH}$ or $V_{IN} \leq V_{IL}$, $f = f_{MAX}$		40		40	mA
I_{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V_{CC} , $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$, or $V_{IN} \leq 0.3V$, $f = 0$	Com'l/Ind'l		8	8	mA
			Com'l	L	0.5	0.5	

Notes:

- $V_{IL}(\text{min.}) = -2.0V$ for pulse durations of less than 20 ns.
- T_A is the "Instant On" case temperature.

Electrical Characteristics Over the Operating Range (continued)

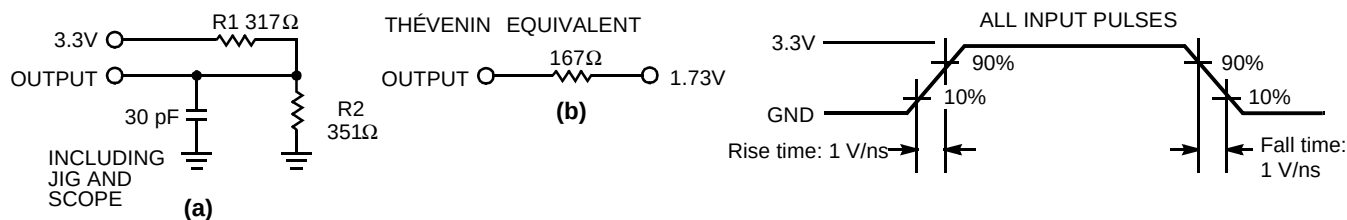
Parameter	Description	Test Conditions		-17		-20		-25		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = −4.0 mA		2.4		2.4		2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 mA			0.4		0.4		0.4	V
V _{IH}	Input HIGH Voltage			2.2	V _{CC} + 0.5	2.2	V _{CC} + 0.5	2.2	V _{CC} + 0.5	V
V _{IL}	Input LOW Voltage ^[1]			−0.5	0.8	−0.5	0.8	−0.5	0.8	V
I _{IX}	Input Load Current	GND ≤ V _I ≤ V _{CC}		−1	+1	−1	+1	−1	+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _{OUT} ≤ V _{CC} , Output Disabled		−1	+1	−1	+1	−1	+1	μA
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max., f = f _{MAX} = 1/t _{RC}	Comm'l		160		150		130	mA
			Ind'l		180		170		150	
I _{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V _{CC} , CE ≥ V _{IH} V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}			40		40		40	mA
I _{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V _{CC} , CE ≥ V _{CC} − 0.3V, V _{IN} ≥ V _{CC} − 0.3V, or V _{IN} ≤ 0.3V, f=0		Com'l/Ind'l			8		8	mA
			Com'l	L		0.5		0.5		0.5

Capacitance^[3]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	$T_A = 25^\circ\text{C}, f = 1 \text{ MHz}, V_{CC} = 3.3\text{V}$	8	pF
C_{OUT}	I/O Capacitance		8	pF

Note:

3. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms


Switching Characteristics^[4] Over the Operating Range

Parameter	Description	-12		-15		-17		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE								
t _{RC}	Read Cycle Time	12		15		17		ns
t _{AA}	Address to Data Valid		12		15		17	ns
t _{OHA}	Data Hold from Address Change	3		3		3		ns
t _{ACE}	$\overline{\text{CE}}$ LOW to Data Valid		12		15		17	ns
t _{DOE}	$\overline{\text{OE}}$ LOW to Data Valid		6		7		8	ns
t _{LZOE}	$\overline{\text{OE}}$ LOW to Low Z	0		0		0		ns
t _{HZOE}	$\overline{\text{OE}}$ HIGH to High Z ^[5, 6]		6		7		7	ns
t _{LZCE}	$\overline{\text{CE}}$ LOW to Low Z ^[6]	3		3		3		ns
t _{HZCE}	$\overline{\text{CE}}$ HIGH to High Z ^[5, 6]		6		7		7	ns
t _{PU}	$\overline{\text{CE}}$ LOW to Power-Up	0		0		0		ns
t _{PD}	$\overline{\text{CE}}$ HIGH to Power-Down		12		15		17	ns
t _{DBE}	Byte Enable to Data Valid		6		7		7	ns
t _{LZBE}	Byte Enable to Low Z	0		0		0		ns
t _{HZBE}	Byte Disable to High Z		6		7		8	ns
WRITE CYCLE ^[7, 8]								
t _{WC}	Write Cycle Time	12		15		17		ns
t _{SCE}	$\overline{\text{CE}}$ LOW to Write End	10		12		12		ns
t _{AW}	Address Set-Up to Write End	10		12		12		ns
t _{HA}	Address Hold from Write End	0		0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		0		ns
t _{PWE}	$\overline{\text{WE}}$ Pulse Width	10		12		12		ns
t _{SD}	Data Set-Up to Write End	7		8		9		ns
t _{HD}	Data Hold from Write End	0		0		0		ns
t _{LZWE}	$\overline{\text{WE}}$ HIGH to Low Z ^[6]	3		3		3		ns
t _{HZWE}	$\overline{\text{WE}}$ LOW to High Z ^[5, 6]		6		7		8	ns
t _{BW}	Byte Enable to End of Write	10		12		12		ns

Notes:

- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
- t_{HZOE} , t_{HZCE} , and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ± 500 mV from steady-state voltage.
- At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
- The internal write time of the memory is defined by the overlap of $\overline{CE}$ LOW, and $\overline{WE}$ LOW. $\overline{CE}$ and $\overline{WE}$ must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
- The minimum write cycle time for Write Cycle No. 3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD} .

Switching Characteristics^[4] Over the Operating Range (continued)

Parameter	Description	-20		-25		Unit
		Min.	Max.	Min.	Max.	
READ CYCLE						
t _{RC}	Read Cycle Time	20		25		ns
t _{AA}	Address to Data Valid		20		25	ns
t _{OHA}	Data Hold from Address Change	3		5		ns
t _{ACE}	$\overline{\text{CE}}$ LOW to Data Valid		20		25	ns
t _{DOE}	$\overline{\text{OE}}$ LOW to Data Valid		8		10	ns
t _{LZOE}	$\overline{\text{OE}}$ LOW to Low Z	0		0		ns
t _{HZOE}	$\overline{\text{OE}}$ HIGH to High Z ^[5, 6]		8		10	ns
t _{LZCE}	$\overline{\text{CE}}$ LOW to Low Z ^[6]	3		5		ns
t _{HZCE}	$\overline{\text{CE}}$ HIGH to High Z ^[5, 6]		8		10	ns
t _{PU}	$\overline{\text{CE}}$ LOW to Power-Up	0		0		ns
t _{PD}	$\overline{\text{CE}}$ HIGH to Power-Down		20		25	ns
t _{DBE}	Byte Enable to Data Valid		8		10	ns
t _{LZBE}	Byte Enable to Low Z	0		0		ns
t _{HZBE}	Byte Disable to High Z		8		10	ns
WRITE CYCLE ^[7, 8]						
t _{WC}	Write Cycle Time	20		25		ns
t _{SCE}	$\overline{\text{CE}}$ LOW to Write End	13		15		ns
t _{AW}	Address Set-Up to Write End	13		15		ns
t _{HA}	Address Hold from Write End	0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		ns
t _{PWE}	$\overline{\text{WE}}$ Pulse Width	13		15		ns
t _{SD}	Data Set-Up to Write End	9		10		ns
t _{HD}	Data Hold from Write End	0		0		ns
t _{LZWE}	$\overline{\text{WE}}$ HIGH to Low Z ^[6]	3		5		ns
t _{HZWE}	$\overline{\text{WE}}$ LOW to High Z ^[5, 6]		8		10	ns
t _{BW}	Byte Enable to End of Write	13		15		ns

Data Retention Characteristics Over the Operating Range (For L version only)

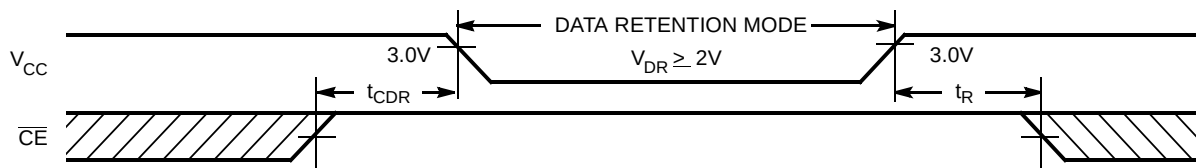
Parameter	Description	Conditions ^[10]	Min.	Max.	Unit
V_{DR}	V_{CC} for Data Retention		2.0		V
I_{CCDR}	Data Retention Current	$V_{CC} = V_{DR} = 2.0V$, $CE \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$		330	μA
$t_{CDR}^{[3]}$	Chip Deselect to Data Retention Time		0		ns
$t_R^{[9]}$	Operation Recovery Time		t_{RC}		ns

Notes:

9. $t_r \leq 3$ ns for the -12 and -15 speeds. $t_r \leq 5$ ns for the -20 and slower speeds.

10. No input may exceed $V_{CC} + 0.5V$.

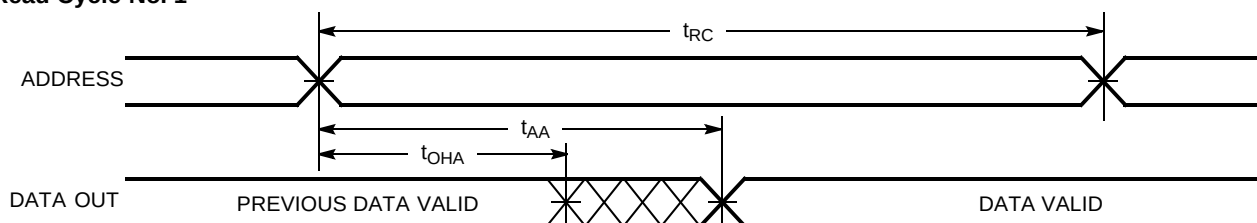
Data Retention Waveform



1041BV33-

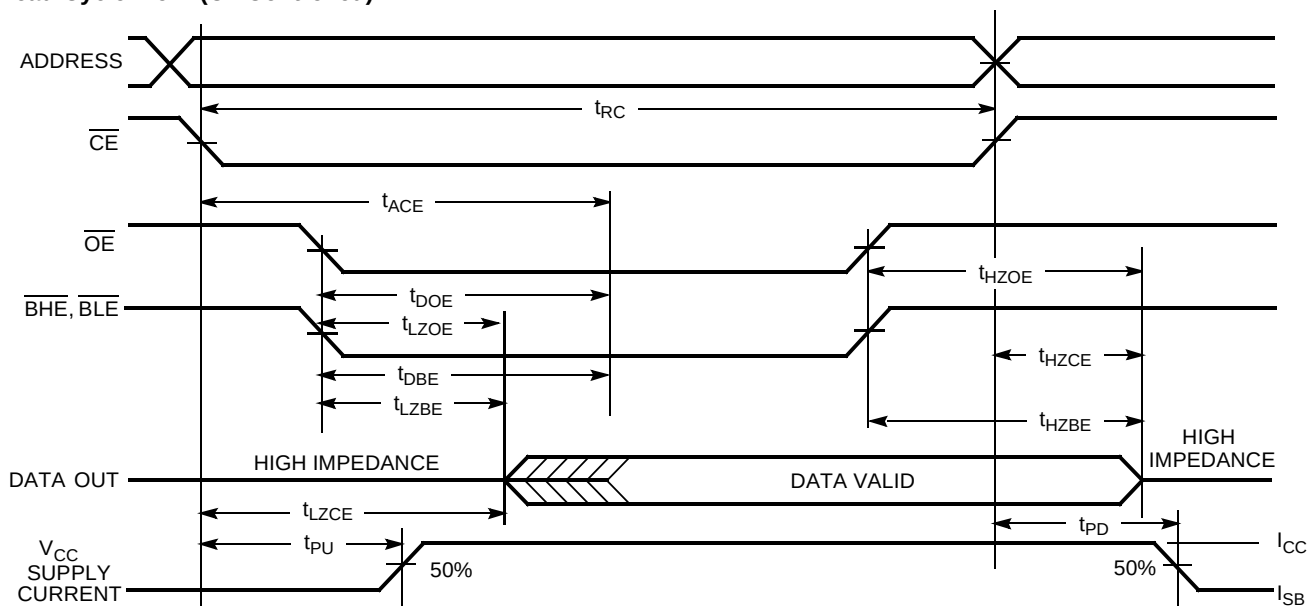
Switching Waveforms

Read Cycle No. 1^[11, 12]



1041BV33-6

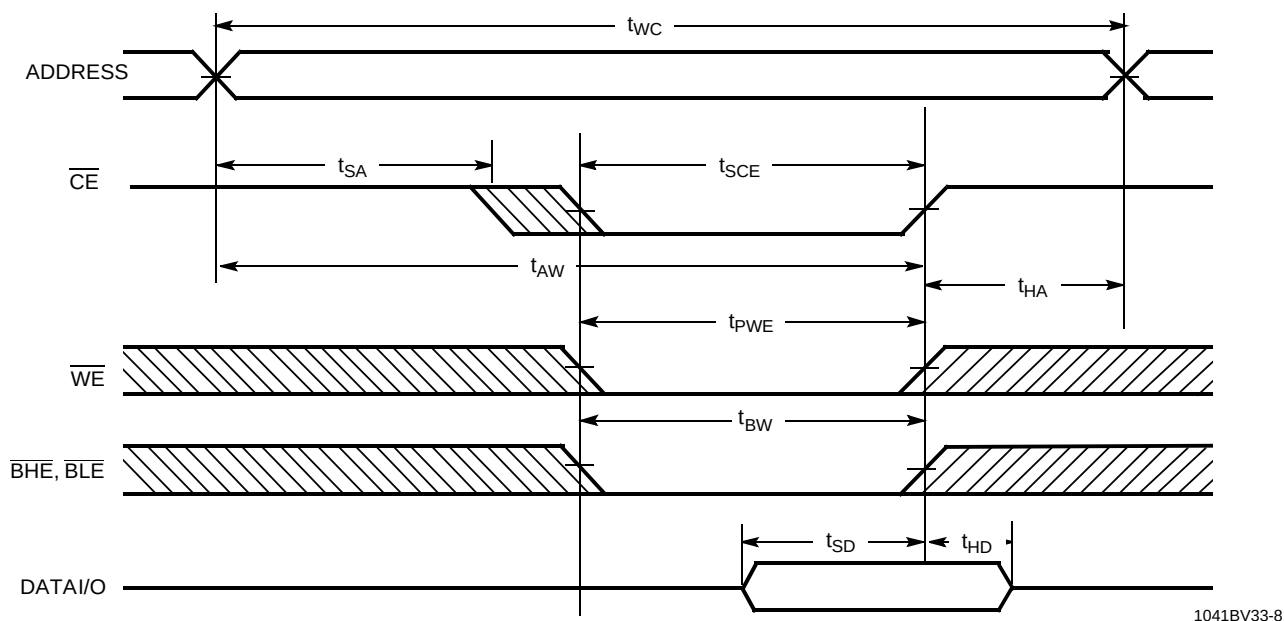
Read Cycle No. 2 (OE Controlled)^[12, 13]



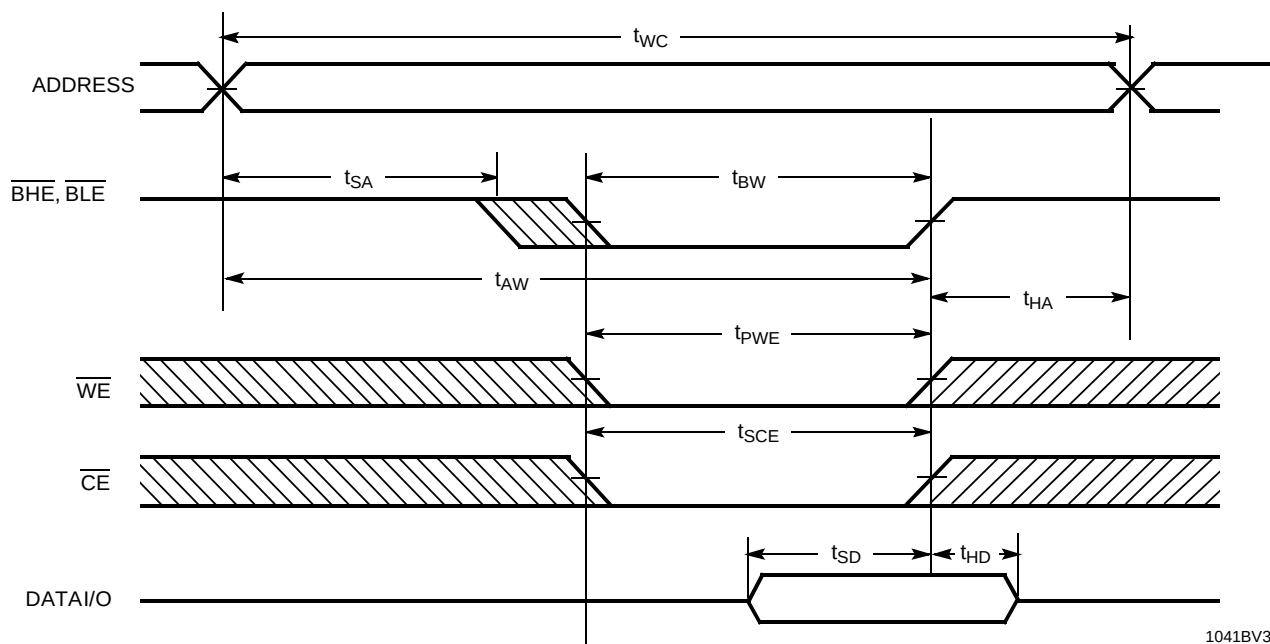
1041BV33-7

Notes:

11. Device is continuously selected. $\overline{OE}$, $\overline{CE}$, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL} .
12. $\overline{WE}$ is HIGH for read cycle.
13. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)
Write Cycle No. 1 ($\overline{\text{CE}}$ Controlled)^[14, 15]


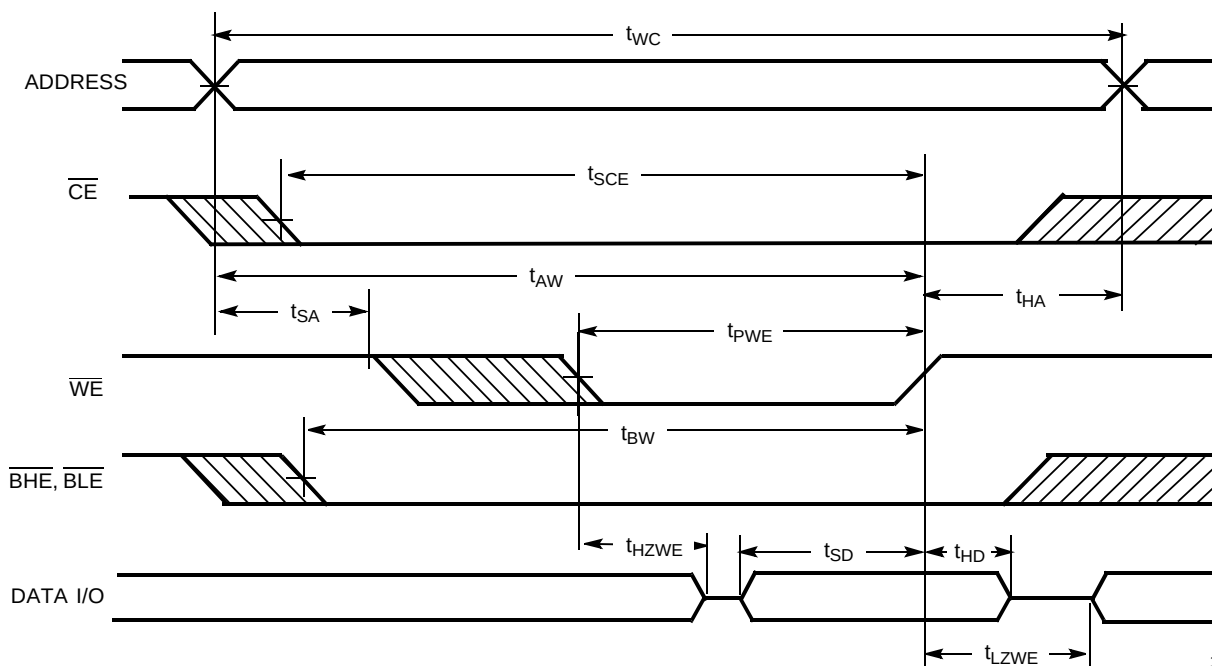
1041BV33-8

Write Cycle No. 2 ($\overline{\text{BLE}}$ or $\overline{\text{BHE}}$ Controlled)


1041BV33-9

Notes:

14. Data I/O is high-impedance if $\overline{\text{OE}}$ or $\overline{\text{BHE}}$ and/or $\overline{\text{BLE}} = V_{IH}$.
15. If $\overline{\text{CE}}$ goes HIGH simultaneously with $\overline{\text{WE}}$ going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)
Write Cycle No.3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)


1041BV33-10

Truth Table

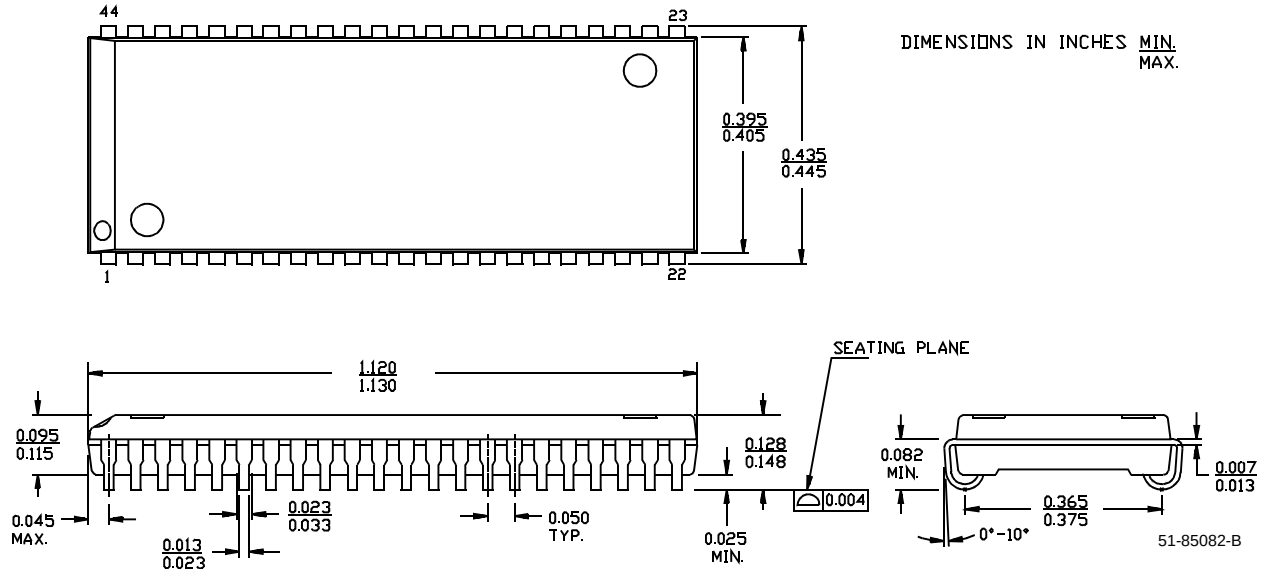
CE	OE	WE	BLE	BHE	I/O ₀ –I/O ₇	I/O ₈ –I/O ₁₅	Mode	Power
H	X	X	X	X	High Z	High Z	Power Down	Standby (I_{SB})
L	L	H	L	L	Data Out	Data Out	Read All Bits	Active (I_{CC})
L	L	H	L	H	Data Out	High Z	Read Lower Bits Only	Active (I_{CC})
L	L	H	H	L	High Z	Data Out	Read Upper Bits Only	Active (I_{CC})
L	X	L	L	L	Data In	Data In	Write All Bits	Active (I_{CC})
L	X	L	L	H	Data In	High Z	Write Lower Bits Only	Active (I_{CC})
L	X	L	H	L	High Z	Data In	Write Upper Bits Only	Active (I_{CC})
L	H	H	X	X	High Z	High Z	Selected, Outputs Disabled	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
12	CY7C1041BV33-12VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-12VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-12ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-12ZC	Z44	44-Pin TSOP II Z44	
15	CY7C1041BV33-15VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-15VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-15ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-15ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33-15VI	V34	44-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1041BV33-15ZI	Z44	44-Pin TSOP II Z44	
17	CY7C1041BV33-17VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-17VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-17ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-17ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33-17VI	V34	44-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1041BV33-17ZI	Z44	44-Pin TSOP II Z44	
20	CY7C1041BV33-20VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-20VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-20ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-20ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33-20VI	V34	44-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1041BV33-20ZI	Z44	44-Pin TSOP II Z44	
25	CY7C1041BV33-25VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1041BV33L-25VC	V34	44-Lead (400-Mil) Molded SOJ	
	CY7C1041BV33-25ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33L-25ZC	Z44	44-Pin TSOP II Z44	
	CY7C1041BV33-25VI	V34	44-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1041BV33-25ZI	Z44	44-Pin TSOP II Z44	

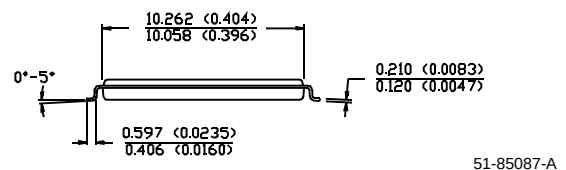
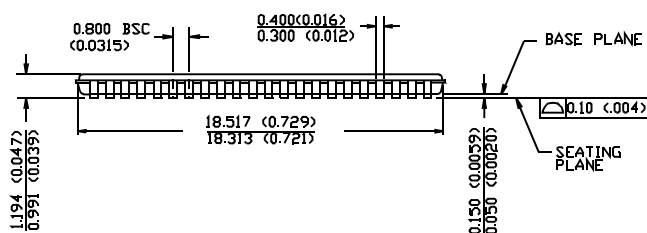
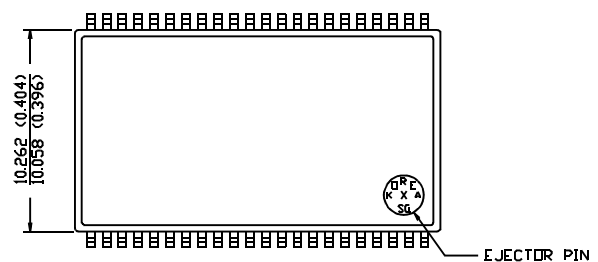
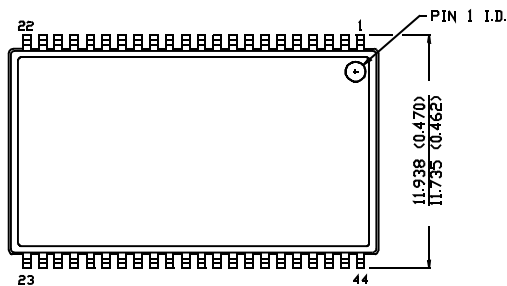
Package Diagrams

44-Lead (400-Mil) Molded SOJ V34



44-Pin TSOP II Z44

DIMENSION IN MM (INCH)
MAX
MIN.



Document Title: CY7C1041BV33 256K x 16 SRAM
Document Number: 38-05168

REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	111840	11/17/01	DSG	Change from Spec number: 38-00932 to 38-05168